BTA208X-800CT

3Q Hi-Com Triac

Rev.03- 03 March 2021 Product data sheet

1. General description

Planar passivated high commutation three quadrant triac in a TO220F "full pack" plastic package. This triac is intended for use in motor control circuits where very high blocking voltage can occur. Rated junction temperature ($T_{j(max)}$ = 150 °C) without the aid of a snubber. It is used in applications where "high junction operating temperature capability" is required.

2. Features and benefits

- High junction operating temperature capability ($T_{j(max)}$ = 150 °C)
- Full cycle AC conduction
- Over-voltage withstand capability to IEC 61000-4-5
- Pin compatible with standard triacs
- Planar passivated for voltage ruggedness and reliability
- Protective self turn-on capability for high energy transients
- Triggering in three quadrants only
- Very high immunity to IEC 61000-4-4 fast transient
- Package meets UL94V0 flammability requirement
- Package is RoHS compliant
- Package meets UL1557 isolation test requirement rated at 2500V RMS

3. Applications

- AC fan, pump and compressor controls
- Highly inductive, resistive and safety loads
- Large and small appliances (White Goods)
- Reversing induction motor controls e.g. vertical axis washing machines
- Applications subject to high temperature ($T_{j(max)}$ = 150 °C)

4. Quick reference data

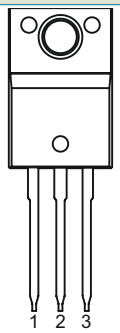
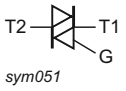
Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage			-	-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_h \leq 103°C$; Fig.1; Fig. 2; Fig. 3		-	-	8	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p =20ms; Fig. 4; Fig. 5		-	-	80	A
		full sine wave; $T_{j(init)}$ = 25 °C; t_p =16.7ms		-	-	88	A
T_j	junction temperature			-	-	150	°C
Static characteristics							
I_{GT}	gate trigger current	V_D = 12 V; I_T = 0.1 A; T2+ G+; T_j = 25 °C; Fig. 7		-	-	35	mA
		V_D = 12 V; I_T = 0.1 A; T2+ G-; T_j = 25 °C; Fig. 7		-	-	35	mA

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
		V_D = 12 V; I_T = 0.1 A; T2- G-; T_j = 25 °C; Fig. 7		-	-	35	mA
I_H	holding current	V_D = 12 V; T_j = 25 °C; Fig. 9		-	-	40	mA
V_T	on-state voltage	I_T = 10 A; T_j = 25 °C; Fig. 10		-	1.25	1.6	V
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit		200	-	-	V/µs
		V_{DM} = 536 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit		100	-	-	V/µs
dI_{com}/dt	rate of change of commutating current	V_{DM} = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 8 A; dV_{com}/dt = 20 V/µs; (snubberless condition); gate open circuit		1	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		
2	T2	main terminal 2		
3	G	gate		
mb	n.c.	mounting base; isolated		

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BTA208X-800CT	TO220F	BTA208X-800CTQ	Tube	50	TO220FE	25-Sep-2020

7. Marking

Table 4. Marking codes

Type number	Marking codes
BTA208X-800CT	BTA208X 800CT

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage			-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 103°C$; Fig.1; Fig. 2; Fig. 3		-	8	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; Fig. 4; Fig. 5		-	80	A
		full sine wave; $T_{j(init)} = 25$ °C; $t_p = 16.7$ ms		-	88	A
I^2t	I^2t for fusing	$t_P = 10$ ms; sine wave pulse		-	32	A^2s
dI_T/dt	rate of rise of on-state current	$I_G = 70$ mA		-	150	A/µs
I_{GM}	peak gate current			-	2	A
P_{GM}	peak gate power			-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period		-	0.5	W
T_{stg}	storage temperature			-40	150	°C
T_j	junction temperature			-	150	°C

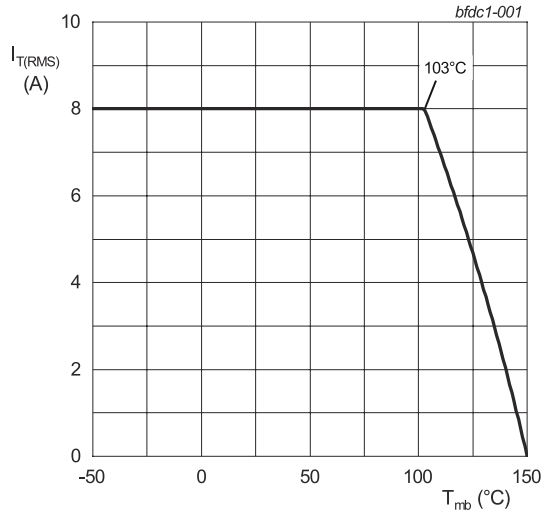
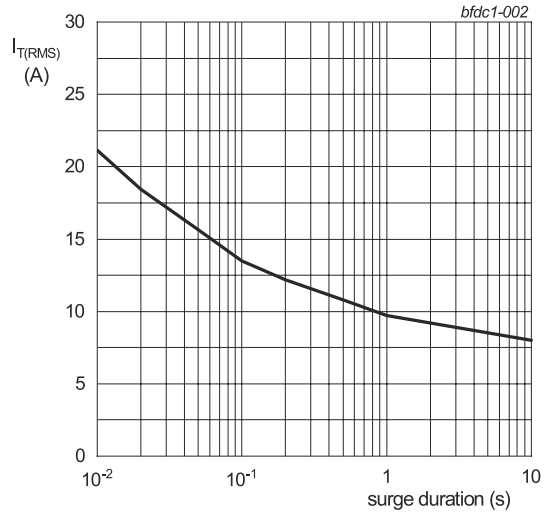
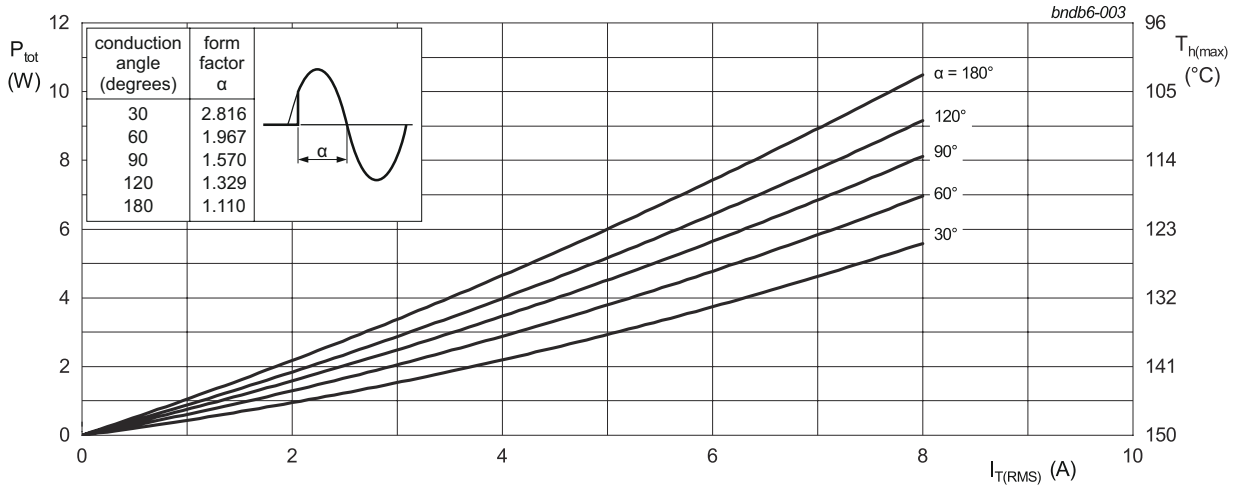


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



f = 50 Hz; T_h =103°C

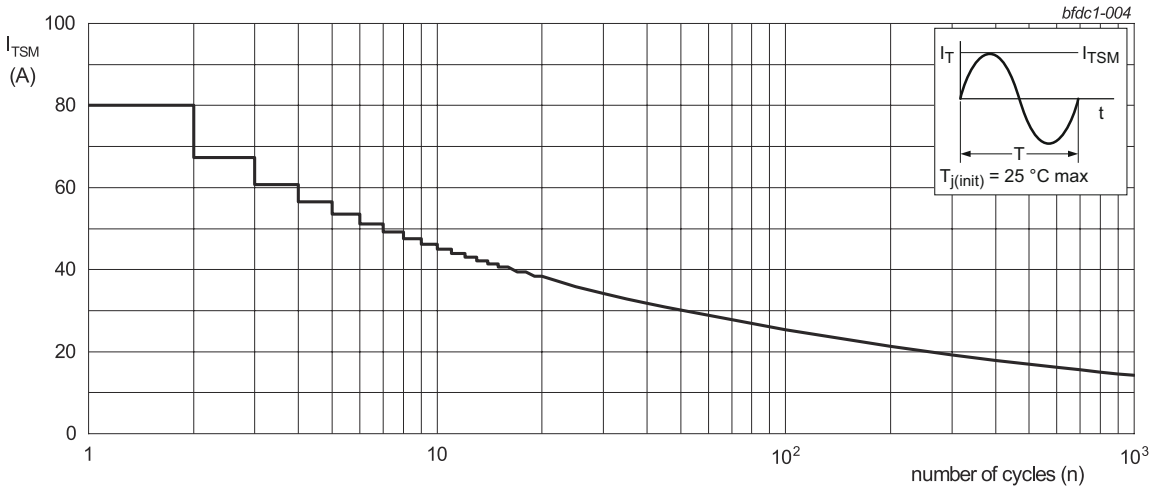
Fig. 2. RMS on-state current as a function of surge duration; maximum values



a = form factor = $I_{T(RMS)}$ / $I_{T(AV)}$

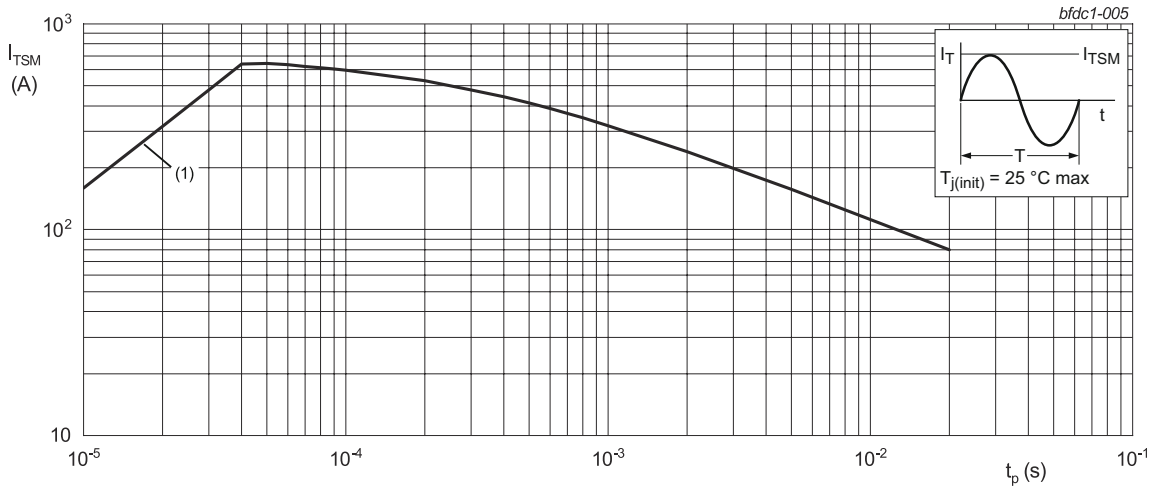
α = conduction angle

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



t_p ≤ 20 ms

(1) dI_T/dt limit

Fig. 5. Non-repetitive peak on-state current as a function of pulse duration; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	full cycle; Fig. 6		-	-	4.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		-	60	-	K/W

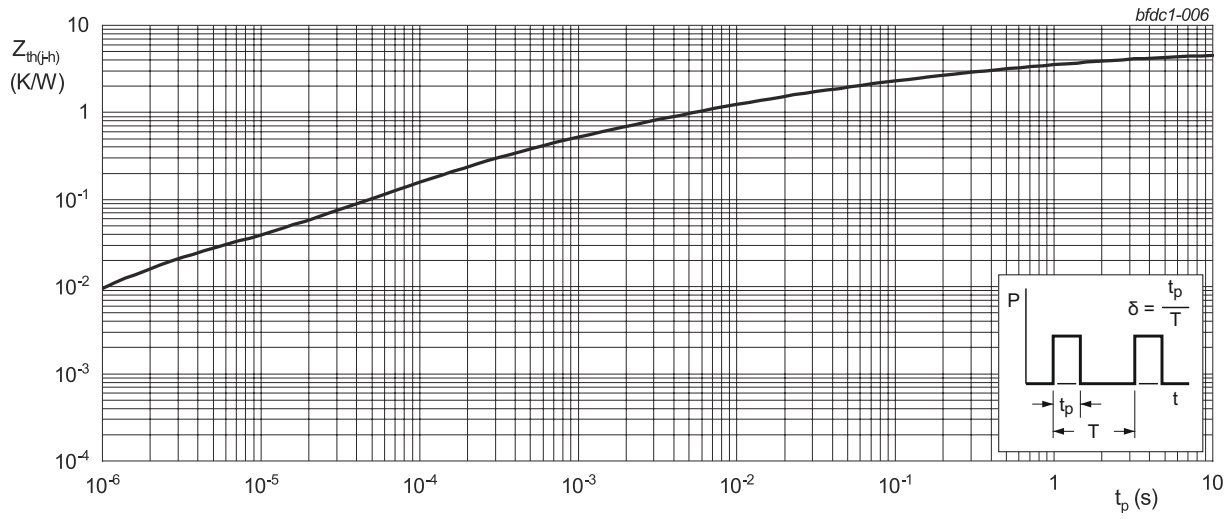


Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse duration

10. Isolation characteristics

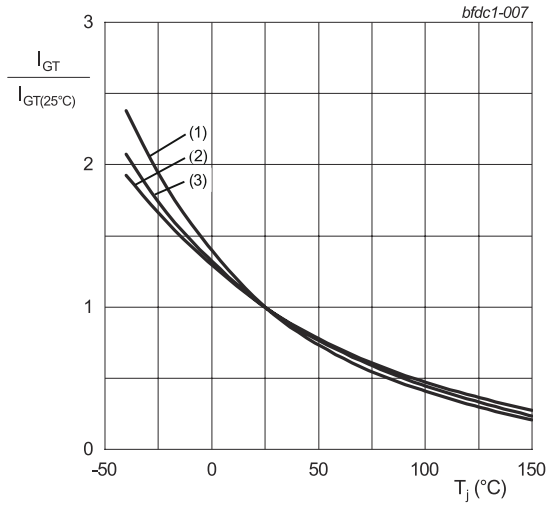
Table 7. Isolation Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; T_{mb} = 25 °C		-	-	2500	V
C_{isol}	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz; T_{mb} = 25 °C		-	10	-	pF

11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	V_D = 12 V; I_T = 0.1 A; T2+ G+; T_j = 25 °C; Fig. 7		-	-	35	mA
		V_D = 12 V; I_T = 0.1 A; T2+ G-; T_j = 25 °C; Fig. 7		-	-	35	mA
		V_D = 12 V; I_T = 0.1 A; T2- G-; T_j = 25 °C; Fig. 7		-	-	35	mA
I_L	latching current	V_D = 12 V; I_G = 0.1 A; T2+ G+; T_j = 25 °C; Fig. 8		-	-	50	mA
		V_D = 12 V; I_G = 0.1 A; T2+ G-; T_j = 25 °C; Fig. 8		-	-	70	mA
		V_D = 12 V; I_G = 0.1 A; T2- G-; T_j = 25 °C; Fig. 8		-	-	50	mA
I_H	holding current	V_D = 12 V; T_j = 25 °C; Fig. 9		-	-	40	mA
V_T	on-state voltage	I_T = 10A; T_j = 25 °C; Fig. 10		-	1.25	1.6	V
V_{GT}	gate trigger voltage	V_D = 12 V; I_T = 0.1 A;T_j = 25 °C Fig. 11		-	0.7	1	V
		V_D = 400V; I_T = 0.1 A;T_j = 150 °C		0.25	0.4	-	V
I_D	off-state current	V_D = 800 V; T_j = 25 °C		-	-	10	µA
		V_D = 800 V; T_j = 150 °C		-	0.3	2	mA
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	V_{DM} = 536V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit		200	-	-	V/µs
		V_{DM} = 536V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit		100	-	-	V/µs
dI_{com}/dt	rate of change of commutating current	V_{DM} = 400 V; T_j = 150 °C;$I_{T(RMS)}$= 8 A; dV_{com}/dt = 20 V/µs; (snubberless condition); gate open circuit		1	-	-	A/ms
		V_{DM} = 400 V; T_j = 150 °C;$I_{T(RMS)}$= 8 A; dV_{com}/dt = 10 V/µs; gate open circuit		1.5	-	-	A/ms
		V_{DM} = 400 V; T_j = 150 °C;$I_{T(RMS)}$= 8 A; dV_{com}/dt = 1 V/µs; gate open circuit		3	-	-	A/ms



(1) T2- G-
(2) T2+ G-
(3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

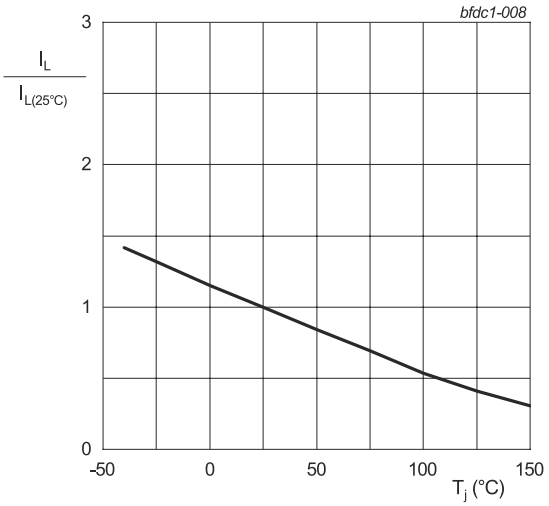


Fig. 8. Normalized latching current as a function of junction temperature

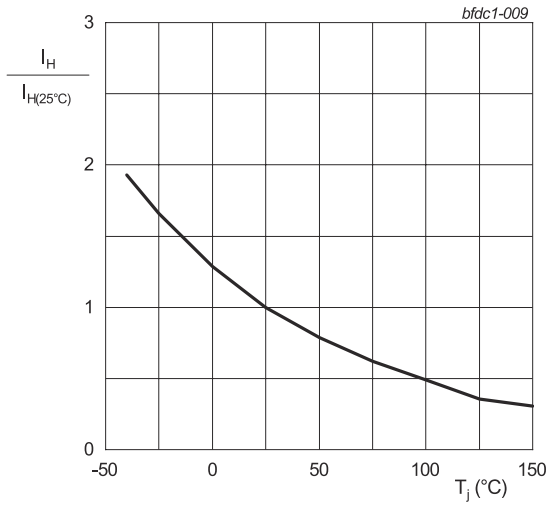
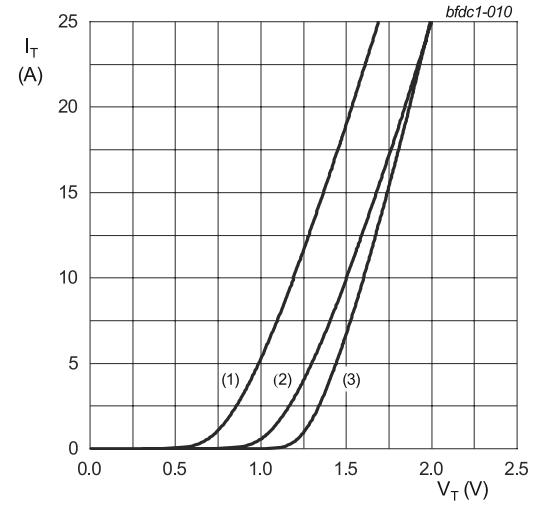


Fig. 9. Normalized holding current as a function of junction temperature



V_o = 1.125 V; R_s = 0.0373Ω
(1) T_j = 150 °C; typical values
(2) T_j = 150 °C; maximum values
(3) T_j = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

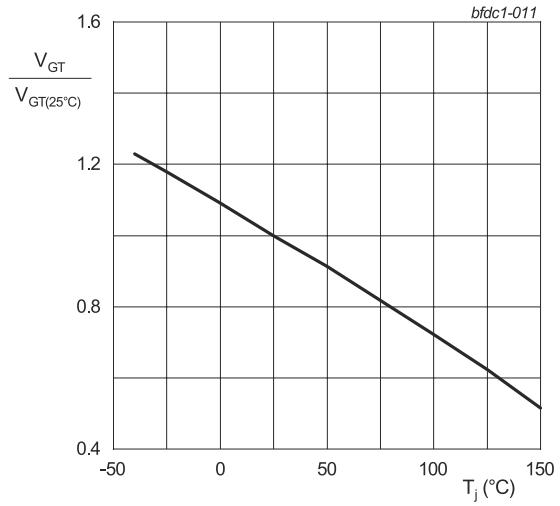


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

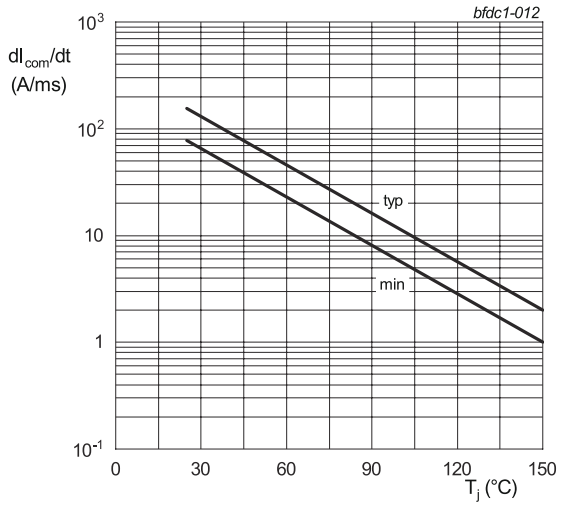
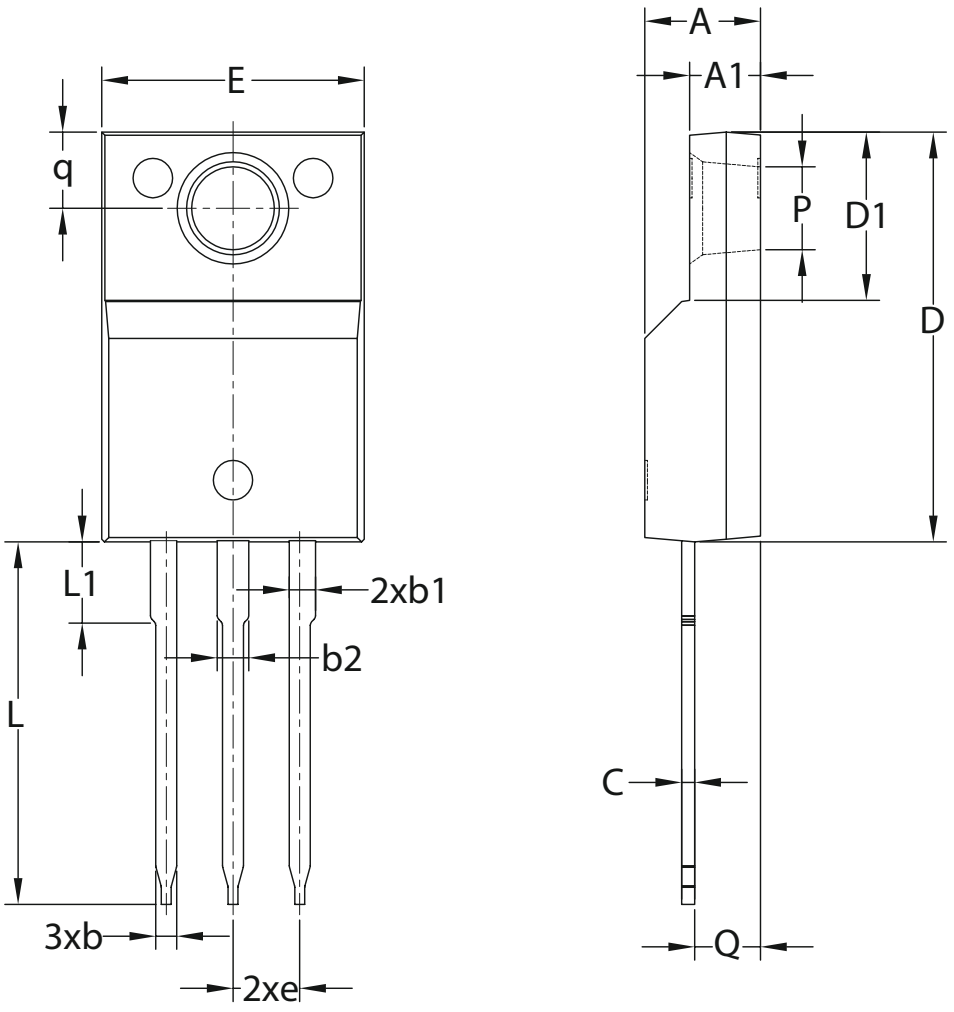


Fig. 12. Rate of change of commutating current as a function of junction temperature; typical and minimum values

12. Package outline

Plastic single-ended package; isolated heatsink mounted;1 mounting hole; 3 leads TO-220 'full pack' TO220F



Unit		A	A1	b	b1	b2	c	D	D1	E	e	L	L1	P	Q	q
MM	min	4.20	2.50	0.70	0.90	1.00	0.40	15.40	6.00	9.70	2.54 (BSC)	13.50	2.80	3.00	2.30	2.60
	max	4.60	2.90	0.90	1.30	1.40	0.60	15.80	6.40	10.30		14.40	3.30	3.30	2.60	3.00

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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